**PNP/NPN Epitaxial Planar Silicon Transistors** 

[CPH6102/6202]



CPH6102/CPH6202

# **High-Current Switching Applications**

**Package Dimensions** 

unit:mm

2146A

## Applications

• DC-DC converter, relay drivers, lamp drivers, motor drivers, strobes.

#### **Features**

- · Adoption of FBET, MBIT processes.
- · High current capacitance.
- · Low collector-to-emitter saturation voltage.
- · High-speed switching.
- Ultrasmall package permitting applied sets to be made small and slim (0.9mm).
- · High allowable power dissipation.

#### (): CPH6102

## **Specifications**

#### Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter		Symbol Conditions	Ratings	Unit
Collector-to-Base Voltage		VCBO	(-)60	V
Collector-to-Emitter Voltage		VCEO	(–)50	V
Emitter-to-Base Voltage		VEBO	(–)5	V
Collector Current	Å		(-)1.0	A
Collector Current (Pulse)	L. Acade .	ICP	(–)2	A
Collector Dissipation	and a set	Pc Mounted on a ceramic board (600mm <sup>2</sup> ×0.8mm)	1.3	W
Junction Temperature	and a second second		150	°C
Storage Temperature	and the second second	Tstg	-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
Falameter			min	typ	max	Ofine
Collector Cutoff Current	Сво /				(–)100	nA
Emitter Cutoff Current	I <sub>EBO</sub> /	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(–)100	nA
DC Current Gain	h <sub>E</sub> E1/	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)100mA	200		560	
DC Current Gain	<sup>β</sup> F£2	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)1A	30			
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)50mA		150		MHz
Output Capacitance	Cob	V <sub>CB</sub> =(-)10V, f=1MHz		(12)8.5		pF

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1: Collector

2 : Collector 3 : Base 4 : Emitter 5 : Collector

6 : Collector SANYO : CPH6

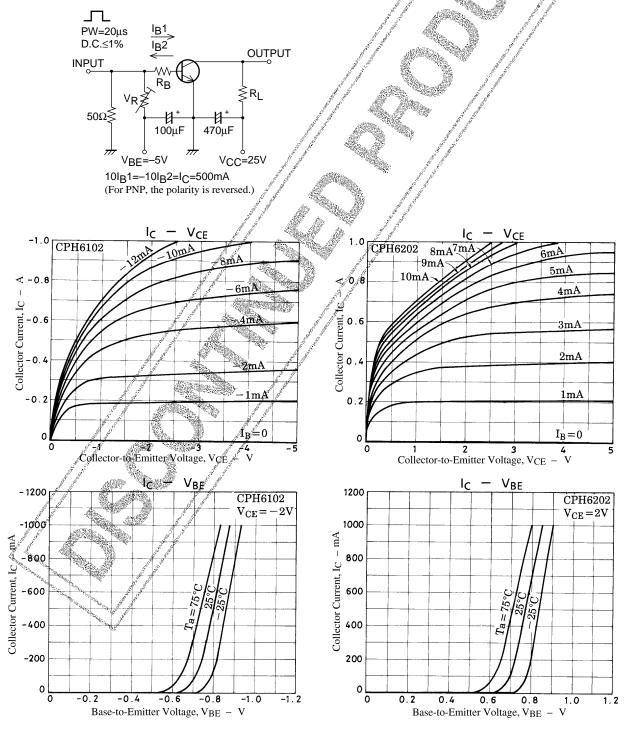
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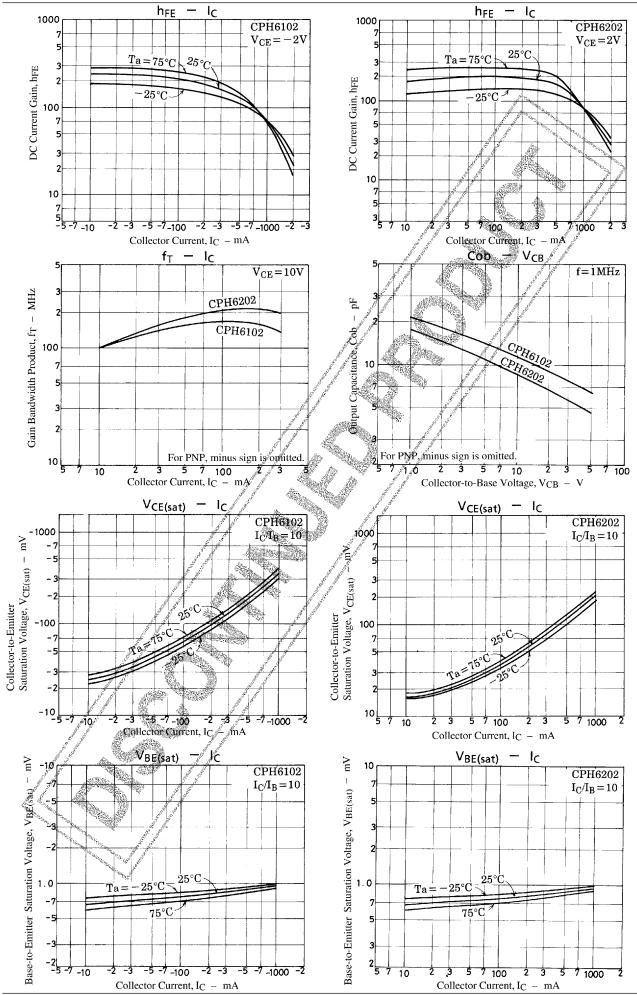
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Parameter	Symbol	Conditions		Ratings		
Falameter	Symbol	Conditions		typ	max	Unit
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)500mA, I <sub>B</sub> =(-)50mA		(-180)	(-500)	mV
			é.	120	300	mV
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)500mA, I <sub>B</sub> =(-)50mA	5	(–)0.9	(–)1.2	V
Collector-to-Base Breakdown Voltage	V <sub>(BR)</sub> CBO	I <sub>C</sub> =(-)10μΑ, I <sub>E</sub> =0	A (+)60	N. N. S.		V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(−)1mA, R <sub>BE</sub> =∞	<i>i</i> (–)50	and the second second	2 Martin Contraction	V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =(-)10μΑ, I <sub>C</sub> =0	(−)5		All Mary and a start of the second	V
Turn-ON Time	ton	See specified test circuit.		40(40)	and the second second	ns
Storage Time	<sup>t</sup> stg	See specified test circuit.		350		🖉 ns
Storage Time		See specified test circuit.		(300)		ns
Fall Time	t <sub>f</sub>	See specified test circuit.		30(30)	And the second second	ns
		and the second	2	95 - J		
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### **Switching Time Test Circuit**



## CPH6102/CPH6202



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## CPH6102/CPH6202

